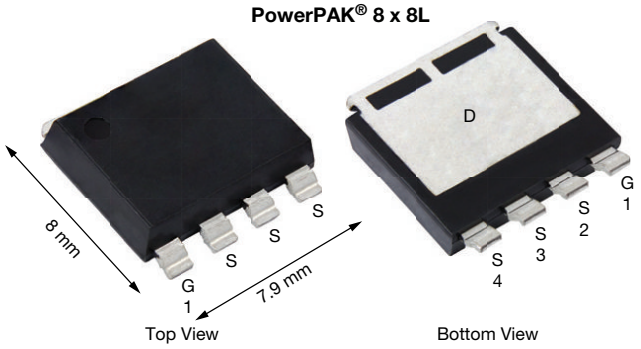
# Automotive P-Channel 40 V (D-S) 175 °C MOSFET



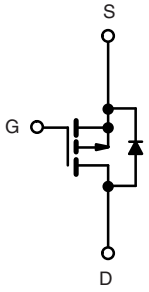

## FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % $R_g$ and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

RoHS COMPLIANT

HALOGEN FREE




P-Channel MOSFET

| PRODUCT SUMMARY | |
|---|---|
| $V_{DS}$ (V) | -40 |
| $R_{DS(on)}$ (Ω) at $V_{GS}$ = -10 V | 0.004 |
| $R_{DS(on)}$ (Ω) at $V_{GS}$ = -4.5 V | 0.0059 |
| $I_D$ (A) [g] | -192 |
| Configuration | Single |

| ORDERING INFORMATION | |
|---|---|
| Package | PowerPAK 8 x 8L |
| Lead (Pb)-free and Halogen-free | SQJQ143EL (for detailed order number please see www.vishay.com/doc?79776) |

**ABSOLUTE MAXIMUM RATINGS** ($T_C$ = 25 °C, unless otherwise noted)

| PARAMETER | | SYMBOL | LIMIT | UNIT |
|---|---|---|---|---|
| Drain-source voltage | | $V_{DS}$ | -40 | V |
| Gate-source voltage [a] | | $V_{GS}$ | ± 20 | |
| Continuous drain current [g] | $T_C$ = 25 °C [b] | $I_D$ | -192 | A |
| | $T_C$ = 125 °C | | -111 | |
| Continuous source current (diode conduction) [b, g] | | $I_S$ | -257 | |
| Pulsed drain current [c, g] | | $I_{DM}$ | -612 | |
| Single pulse avalanche current | L = 0.1 mH | $I_{AS}$ | -58 | |
| Single pulse avalanche energy | | $E_{AS}$ | 171 | mJ |
| Maximum power dissipation [c, g] | $T_C$ = 25 °C | $P_D$ | 283 | W |
| | $T_C$ = 125 °C | | 94 | |
| Operating junction and storage temperature range | | $T_J$, $T_{stg}$ | -55 to +175 | °C |
| Soldering recommendations (peak temperature) [d, e] | | | 260 | |

**THERMAL RESISTANCE RATINGS**

| PARAMETER | | SYMBOL | LIMIT | UNIT |
|---|---|---|---|---|
| Junction-to-ambient | PCB mount [e] | $R_{thJA}$ | 44 | °C/W |
| Junction-to-case (drain) [f] | | $R_{thJC}$ | 0.53 | |

**Notes**

a. Not intended for continuous use with positive gate voltage > 5.0 V
b. Package limited
c. When mounted on 1" square PCB (FR4 material)
d. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
e. Using thermal characterization methods based on JESD51-14
f. Values based on $R_{thJC}$ and $T_C$ of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system

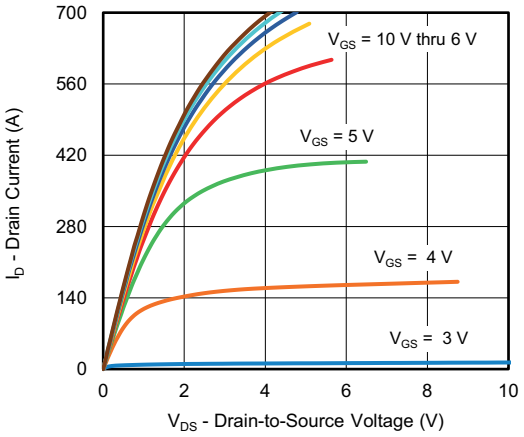
| **SPECIFICATIONS** ($T_C$ = 25 °C, unless otherwise noted) | | | | | | | |
|---|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | | |
| Drain-source breakdown voltage | $V_{DS}$ | $V_{GS}$ = 0, $I_D$ = -250 µA | | -40 | - | - | V |
| Gate-source threshold voltage | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = -250 µA | | -1.5 | -2.0 | -2.5 | |
| Gate-source leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V | | - | - | ± 100 | nA |
| Zero gate voltage drain current | $I_{DSS}$ | $V_{GS}$ = 0 V | $V_{DS}$ = -40 V | - | - | -1 | µA |
| | | $V_{GS}$ = 0 V | $V_{DS}$ = -40 V, $T_J$ = 125 °C | - | - | -50 | |
| | | $V_{GS}$ = 0 V | $V_{DS}$ = -40 V, $T_J$ = 175 °C | - | - | -150 | |
| On-state drain current [a] | $I_{D(on)}$ | $V_{GS}$ = -10 V | $V_{DS}$ ≥ -5 V | -30 | - | - | A |
| Drain-source on-state resistance [a] | $R_{DS(on)}$ | $V_{GS}$ = -10 V | $I_D$ = -15 A | - | 0.0032 | 0.0040 | Ω |
| | | $V_{GS}$ = -10 V | $I_D$ = -15 A, $T_J$ = 125 °C | - | - | 0.0063 | |
| | | $V_{GS}$ = -10 V | $I_D$ = -15 A, $T_J$ = 175 °C | - | - | 0.0076 | |
| | | $V_{GS}$ = -4.5 V | $I_D$ = -15 A | - | 0.0045 | 0.0059 | |
| Forward transconductance [b] | $g_{fs}$ | $V_{DS}$ = -15 V, $I_D$ = -60 A | | - | 160 | - | S |
| **Dynamic [b]** | | | | | | | |
| Input capacitance | $C_{iss}$ | $V_{GS}$ = 0 V | $V_{DS}$ = -25 V, f = 1 MHz | - | 12 969 | 18 157 | pF |
| Output capacitance | $C_{oss}$ | | | - | 810 | 1134 | |
| Reverse transfer capacitance | $C_{rss}$ | | | - | 939 | 1315 | |
| Total gate charge [c] | $Q_g$ | $V_{GS}$ = -10 V | $V_{DS}$ = -20 V, $I_D$ = -30 A | - | 241 | 362 | nC |
| Gate-source charge [c] | $Q_{gs}$ | | | - | 48 | - | |
| Gate-drain charge [c] | $Q_{gd}$ | | | - | 42 | - | |
| Gate resistance | $R_g$ | f = 1 MHz | | 0.8 | 1.7 | 2.6 | Ω |
| Turn-on delay time [c] | $t_{d(on)}$ | $V_{DD}$ = -20 V, $R_L$ = 0.667 Ω, $I_D$ ≅ -30 A, $V_{GEN}$ = -10 V, $R_g$ = 1 Ω | | - | 14 | 21 | ns |
| Rise time [c] | $t_r$ | | | - | 24 | 36 | |
| Turn-off delay time [c] | $t_{d(off)}$ | | | - | 102 | 153 | |
| Fall time [c] | $t_f$ | | | - | 28 | 42 | |
| **Source-Drain Diode Ratings and Characteristics [b]** | | | | | | | |
| Pulsed current [a] | $I_{SM}$ | | | - | - | -612 | A |
| Forward voltage | $V_{SD}$ | $I_F$ = -50 A, $V_{GS}$ = 0 V | | - | -0.8 | -1.1 | V |
| Body diode reverse recovery time | $t_{rr}$ | $I_F$ = -20 A, di/dt = 100 A/µs | | - | 34 | 68 | ns |
| Body diode reverse recovery charge | $Q_{rr}$ | | | - | 34 | 68 | nC |
| Reverse recovery fall time | $t_a$ | | | - | 18 | - | ns |
| Reverse recovery rise time | $t_b$ | | | - | 17 | - | |
| Body diode peak reverse recovery current | $I_{RM(REC)}$ | | | - | -1.9 | - | A |

**Notes**

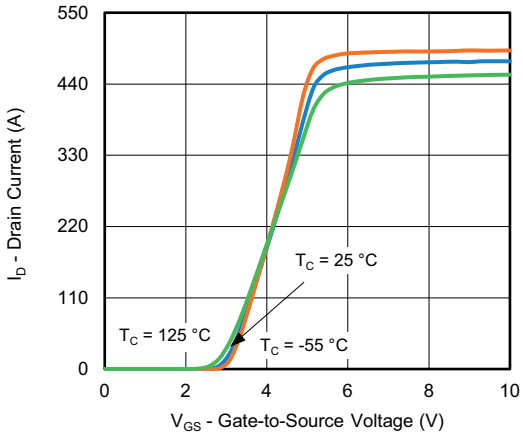
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

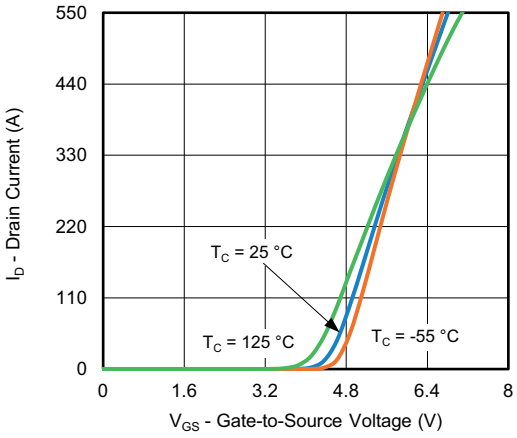
## TYPICAL CHARACTERISTICS ($T_A$ = 25 °C, unless otherwise noted)



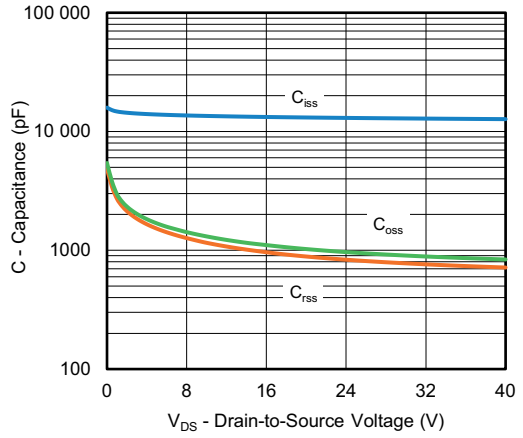

**Output Characteristics**



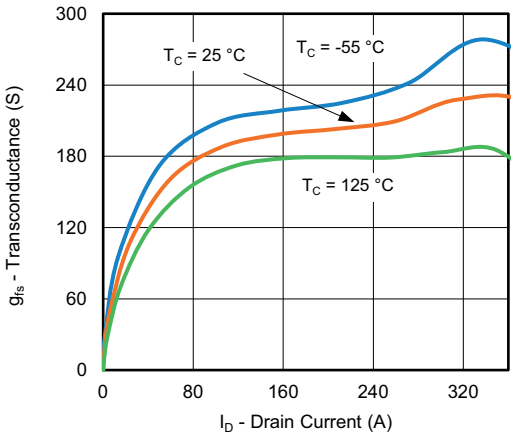

**Transfer Characteristics**



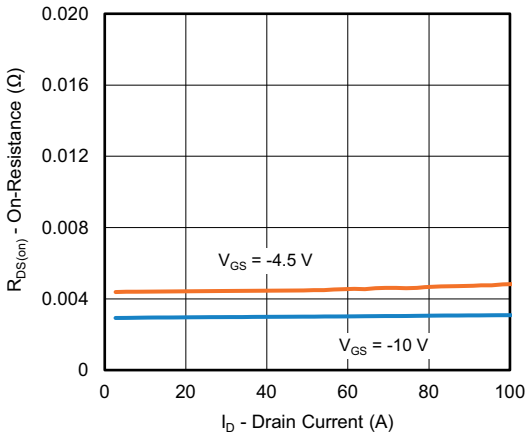

**Transfer Characteristics**




**Capacitance**

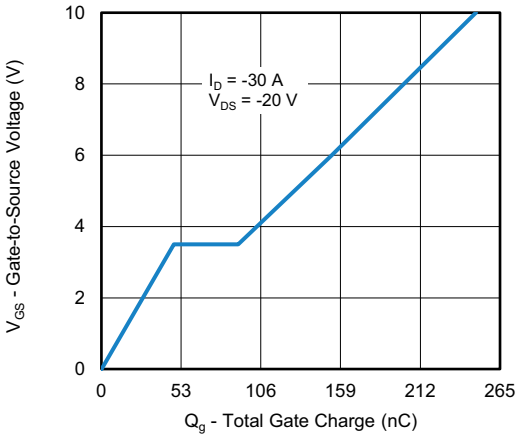



**Transconductance**

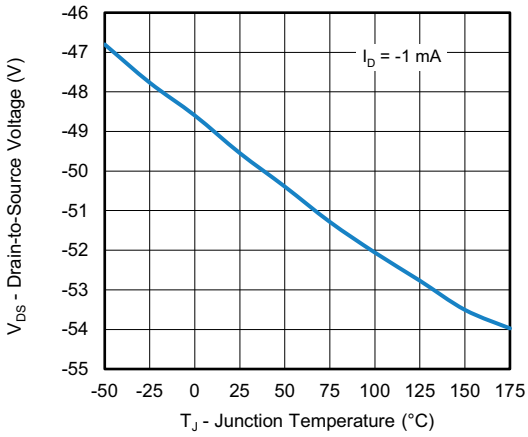



**On-Resistance vs. Drain Current**

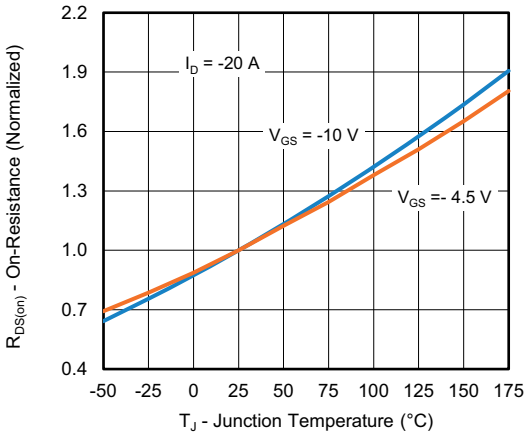
**TYPICAL CHARACTERISTICS** ($T_A$ = 25 °C, unless otherwise noted)



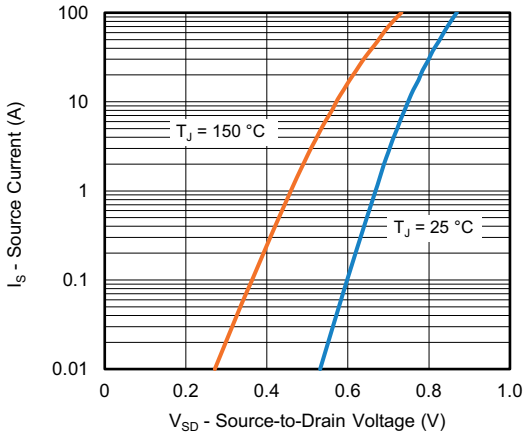

**Gate Charge**



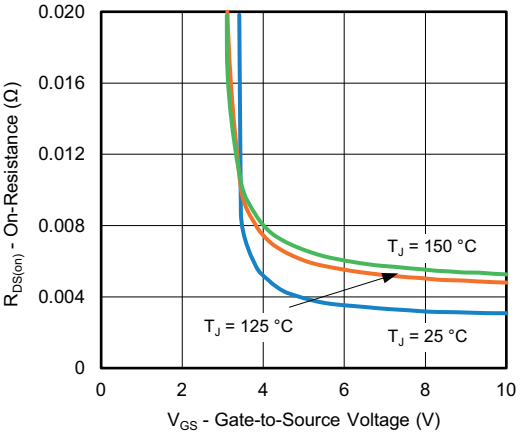

**Drain-Source Breakdown vs. Junction Temperature**



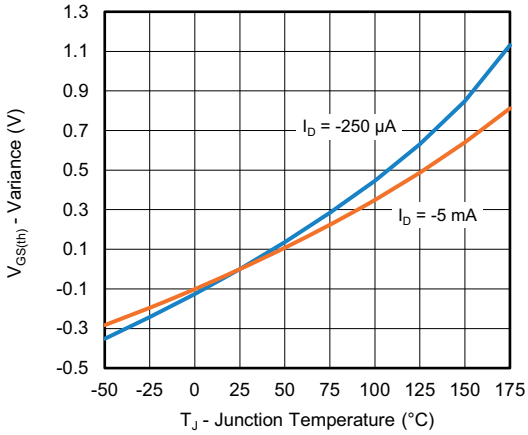

**On-Resistance vs. Junction Temperature**




**Source Drain Diode Forward Voltage**

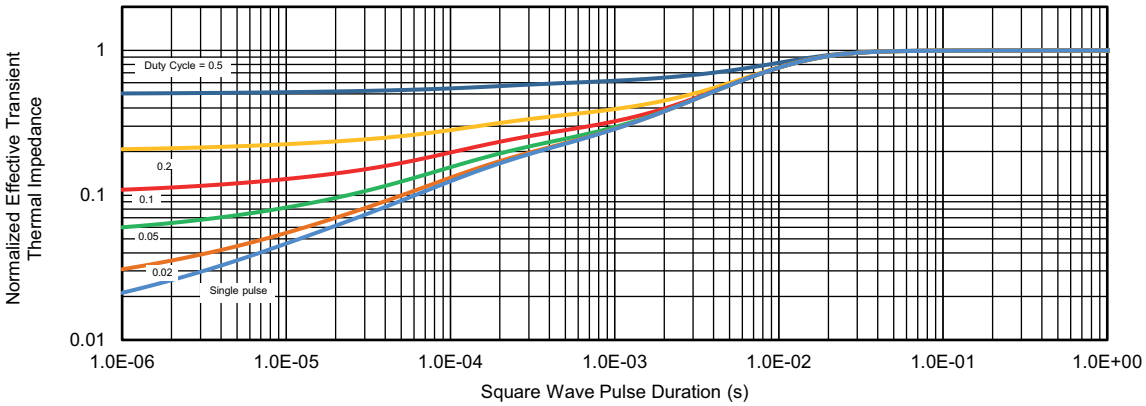



**On-Resistance vs. Gate-to-Source Voltage**

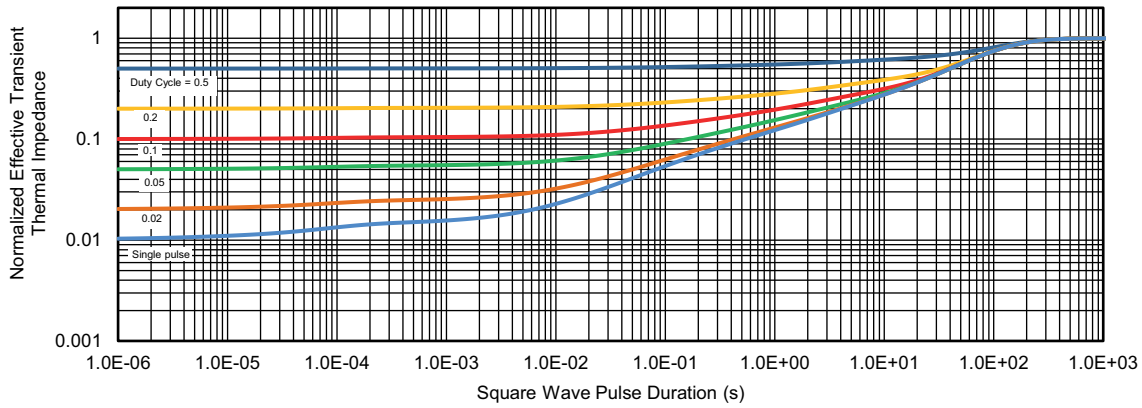



**Threshold Voltage**

**THERMAL RATINGS** ($T_C$ = 25 °C, unless otherwise noted)




**Normalized Thermal Transient Impedance, Junction-to-Case**




**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**Note**

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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